



## **Electroplating Through Holes with Different Geometry -- A Novel and High Productivity Process for Through Hole Fill Plating**

**October 2012**



# OUTLINE

**1 TOPIC**

**2 CHEMISTRY**

**3 FILL PERFORMANCE**

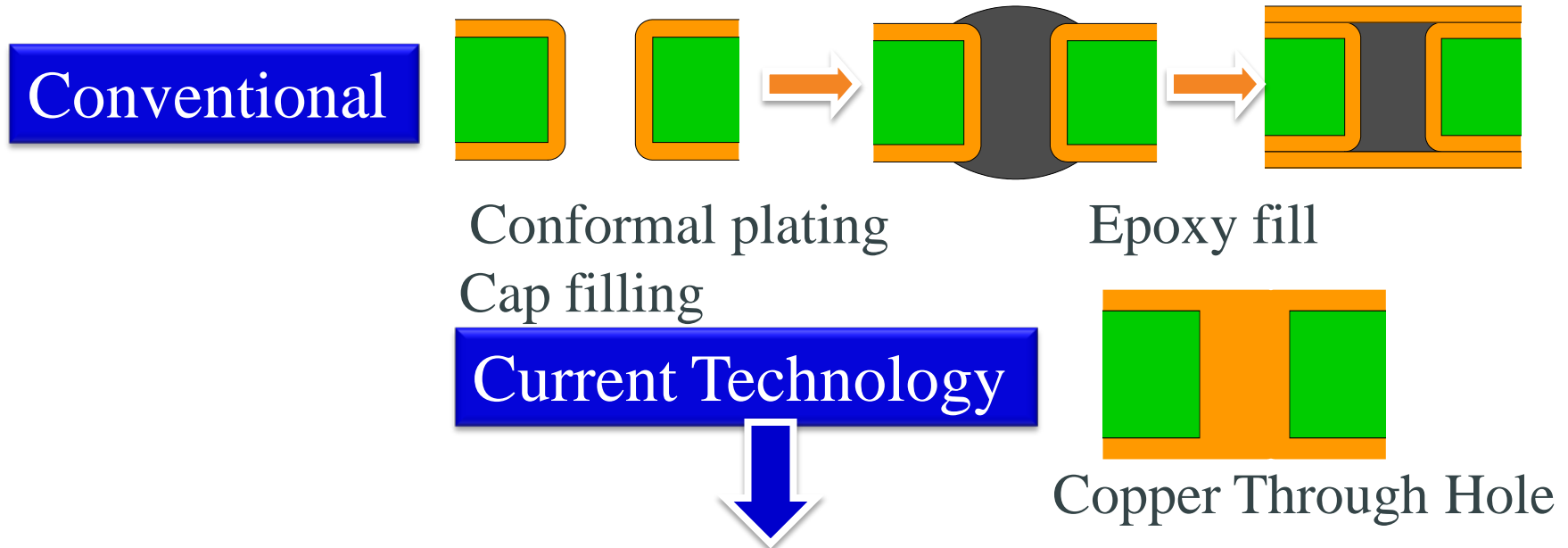
**4 PHYSICAL PROPERTIES & RELIABILITY**

**5 CONCLUSIONS**

## TOPIC

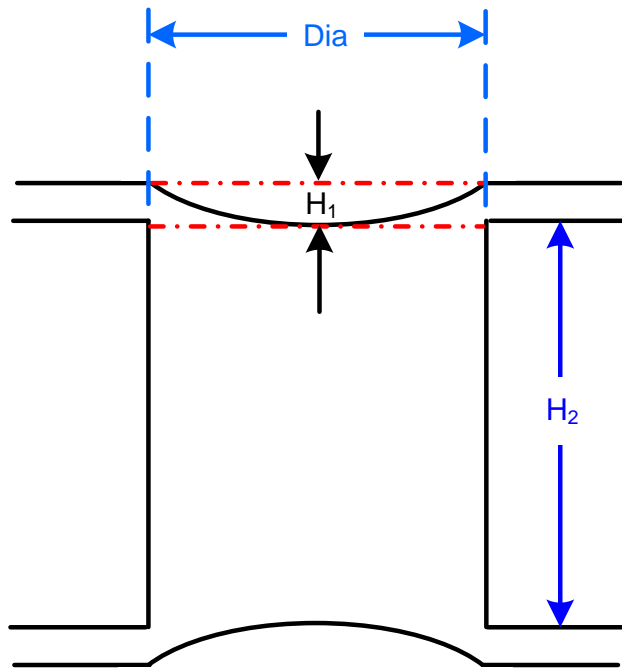
- Background
- Copper Through Hole Fill Capability
- Formulation
- Effects of hole geometry
- Effects of process parameters
- Substrate and metallization effects
- Pilot scale cycling test
- Physical properties and reliability
- Summary

# Through-hole Fill Build-up Process

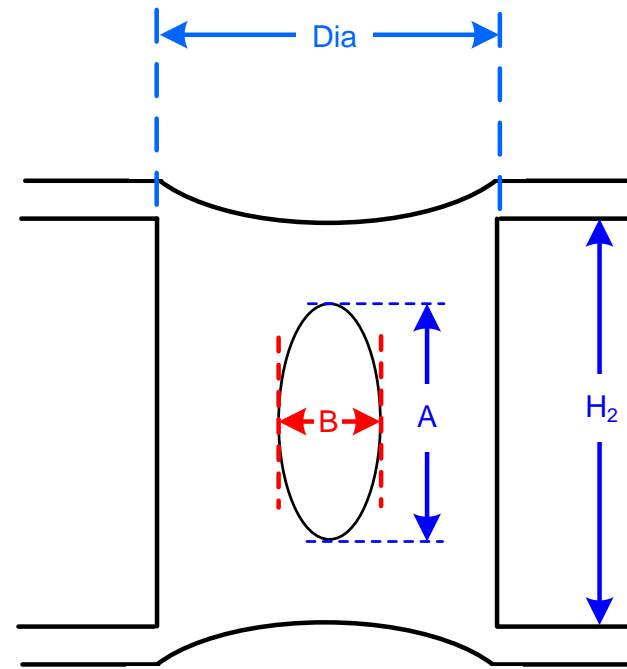


- Highly conductive, improved thermal properties
- Excellent copper to copper adhesion, providing improved reliability
- No CTE mismatch within filled via structure
- Increased productivity and reduced costs

# Copper Through Hole Fill Performance Metrics



- Dimple Depth =  $H_1$
- Aspect Ratio =  $H_2/\text{Dia}$



- Void Area =  $0.5A \times 0.5B \times \pi$
- Hole Area =  $H_2 \times \text{Dia}$
- % Void Area =  $\text{Void Area}/\text{Hole Area} \times 100\%$

# Product Capability

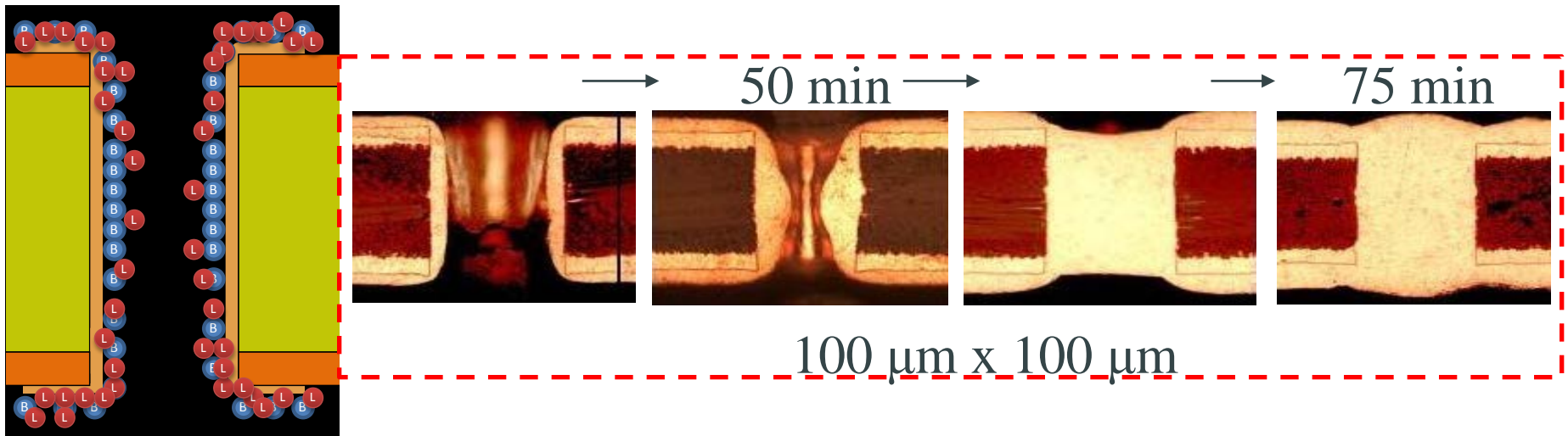
## MICROFILL™ THF Bath Key Capabilities:

- Substrate Thickness : 100  $\mu\text{m}$  – 200  $\mu\text{m}$
- Hole Diameter : 75  $\mu\text{m}$  – 100  $\mu\text{m}$
- Hole Geometry : Mechanical and laser drilled
- Rectification : Direct Current
- Current Density : 10 – 25 A/ft<sup>2</sup> (1 - 2.5ASD)
- Dimple Depth :  $\leq 10 \mu\text{m}$
- Plated Copper Thickness :  $\leq 25 \mu\text{m}$
- Temperature : 20° C to 25° C (68 – 77° F)
- Substrate Metallization : Electroless Copper
- Compatible with Insoluble Anodes
- Panel and Pattern Plate Compatible
- CVS Analysis for all Organic Components

# Optimized Formulation

## Single Step DC Plating – MICROFILL™ THF Bath

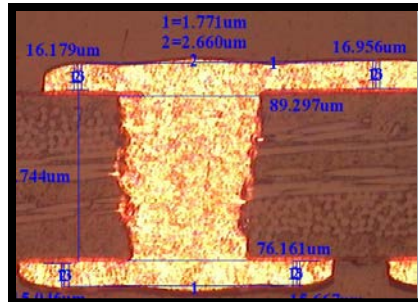
Operating Parameters	Range	Recommended
Copper Sulfate Pentahydrate	220 – 230 g/L	225 g/L
Sulfuric Acid	35 - 45 g/L	40 g/L
Chloride	40 – 60 mg/L	50 mg/L
MICROFILL™ THF Brightener Solution	5.0 - 6.5 mL/L	5.75 mL/L
MICROFILL™ THF Carrier Solution	10 – 15 mL/L	12.5 mL/L
MICROFILL™ THF Leveler Solution	2.25 – 3.25 mL/L	2.75 mL/L



# Impact of Through Hole Geometry

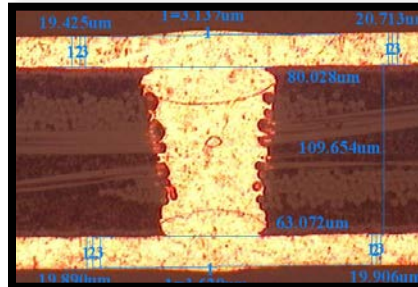
MICROFILL™ THF Bath is Capable of Filling Through Hole (TH) with Range of Different Shapes :

## -Double Sided Laser Through Hole (DSLTH)



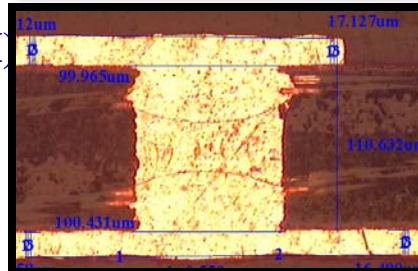
Ø80µm x 100µm

## -One Sided Laser Through Hole (OSLTH)



Ø80µm x 100µm

## -Mechanically Drilled Through Hole (MDTH)



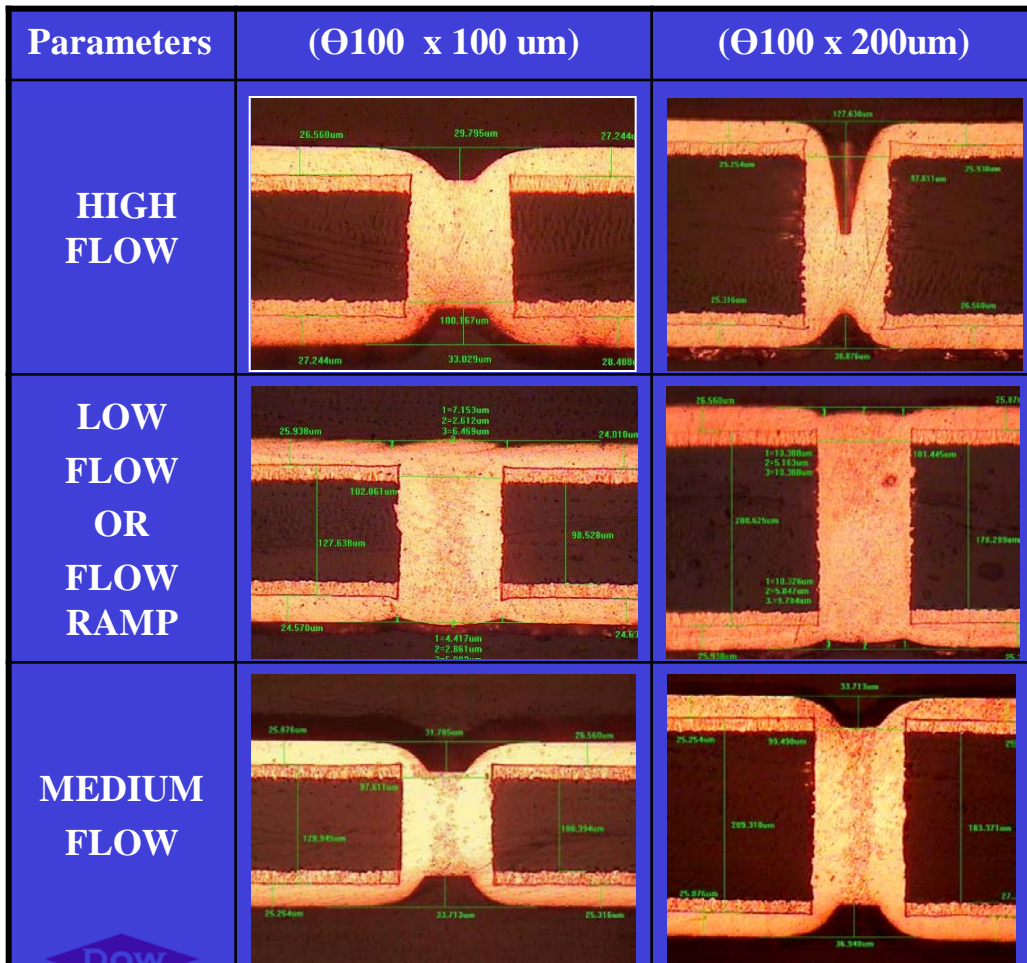
Ø100µm x 100µm

*Easier to Fill*  
*Harder to Fill*

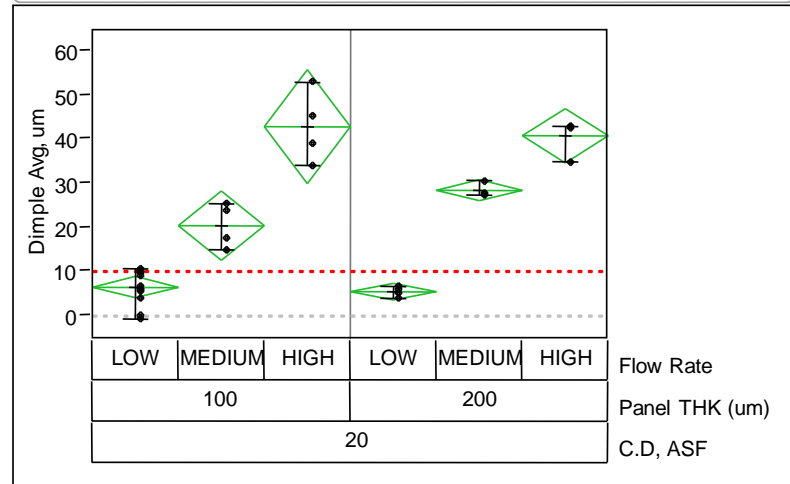


# Effect of Jet Impingement Flow Rate

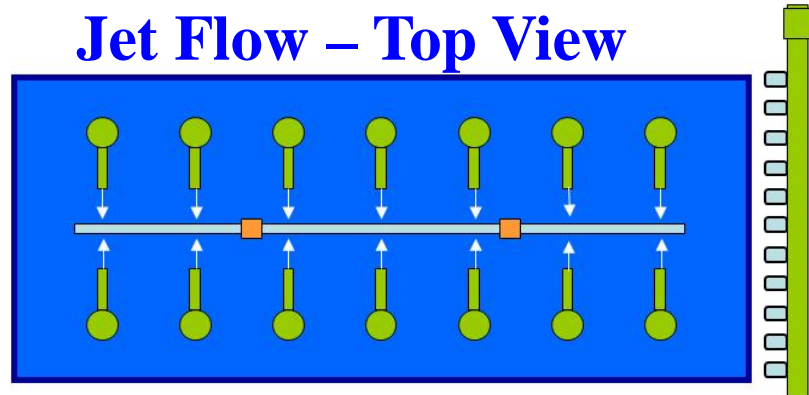
Excessive solution flow increases dimple depth



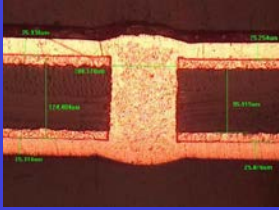
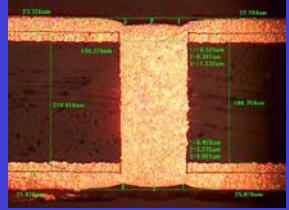
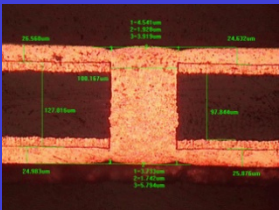
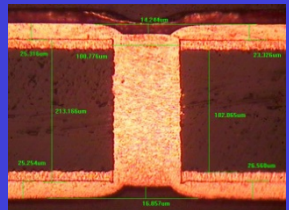
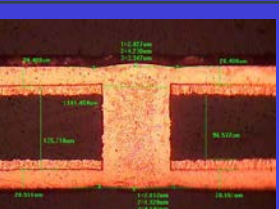
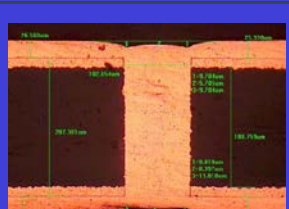
Variability Chart for Dimple Avg,  $\mu\text{m}$



## Jet Flow – Top View

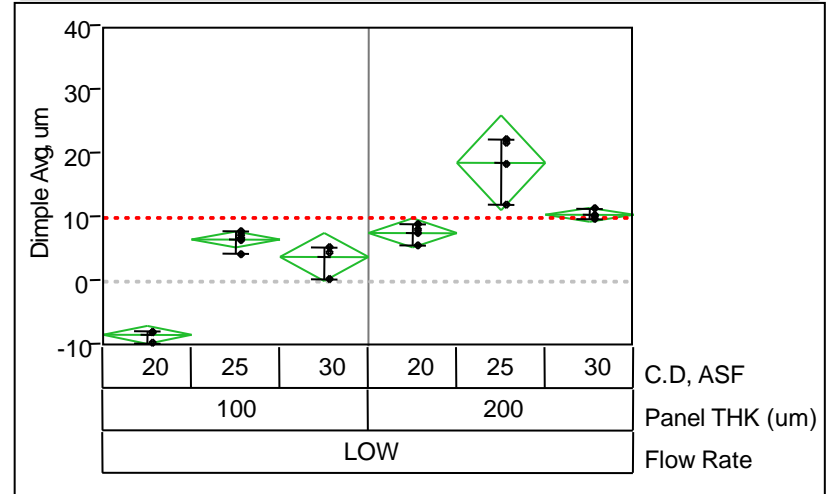


# Effect of Current Density

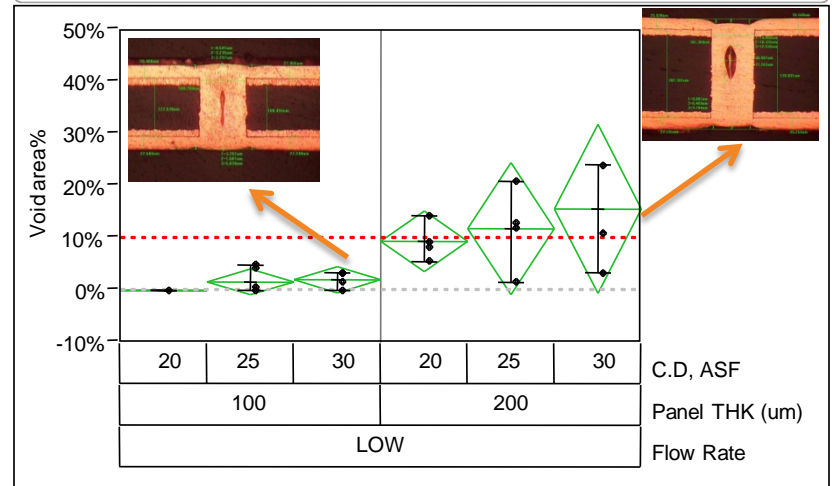
Parameters	( $\text{\O}100\mu\text{m} \times 100\mu\text{m}$ )	( $\text{\O}100\mu\text{m} \times 200\mu\text{m}$ )
<b>CD: 20 ASF</b> Flow: LOW		
<b>CD: 25 ASF</b> Flow: LOW		
<b>CD: 30 ASF</b> Flow: LOW		

- Process performs very well at high current densities, dimple  $< 10 \mu\text{m}$
- Low current density improves TH void performance with  $200 \mu\text{m}$  thick panels
- The small loss of fill performance due to increasing current density is greater at higher substrate thicknesses

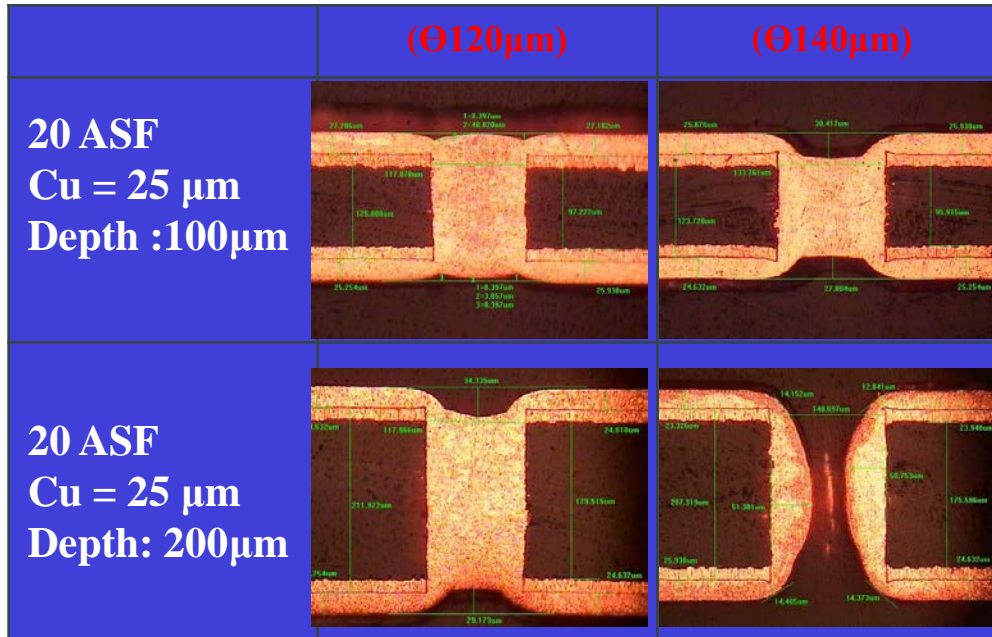
Variability Chart for Dimple Avg,  $\mu\text{m}$



Variability Chart for Void area%



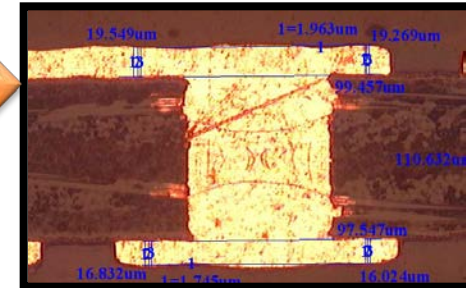
# Effect of Hole Diameter & Copper Thickness on Fill



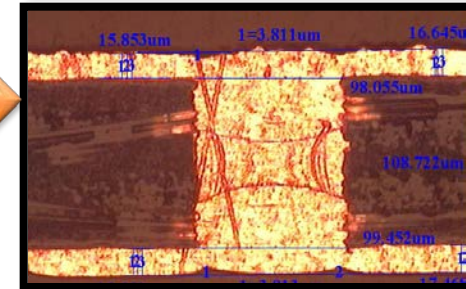
- The amount of plated copper to achieve a completely filled TH is dependent on hole size. Less plated copper is required to fill smaller diameter holes than larger diameter holes
- Depending on geometry size, MICROFILL™ THF bath is capable of filling through holes with copper thickness less than 20  $\mu\text{m}$ .



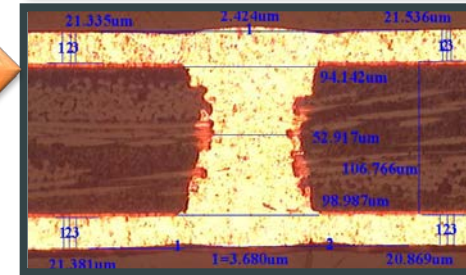
MDTH  
100  $\mu\text{m}$  x 100 $\mu\text{m}$   
Cu = 20 $\mu\text{m}$   
Dimple = 2 $\mu\text{m}$



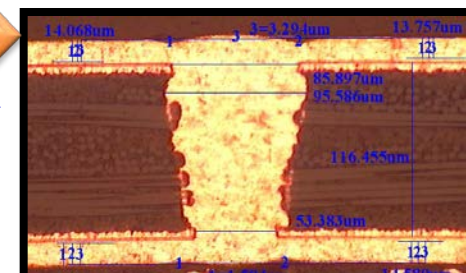
MDTH  
100  $\mu\text{m}$  x 100 $\mu\text{m}$   
Cu = 16 $\mu\text{m}$   
Dimple = 4 $\mu\text{m}$



DSLTH  
100  $\mu\text{m}$  x 100 $\mu\text{m}$   
Cu = 22 $\mu\text{m}$   
Dimple = 0 $\mu\text{m}$



OSLTH  
100  $\mu\text{m}$  x 100 $\mu\text{m}$   
Cu = 17 $\mu\text{m}$   
Dimple = 2 $\mu\text{m}$



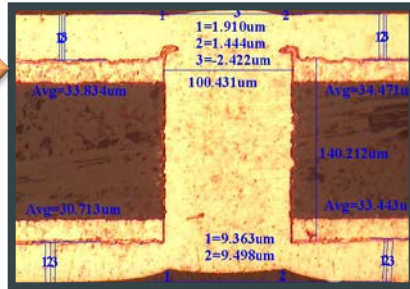
# Impact of Substrate Metallization on Fill

## MDTH

100 $\mu$ m x 100 $\mu$ m

Electroless thickness:

0.5-1.25  $\mu$ m

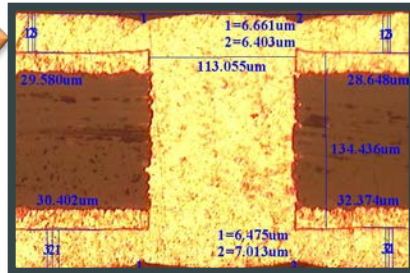


## MDTH

100  $\mu$ m x 100 $\mu$ m

Electroless thickness:

0.2-0.5  $\mu$ m

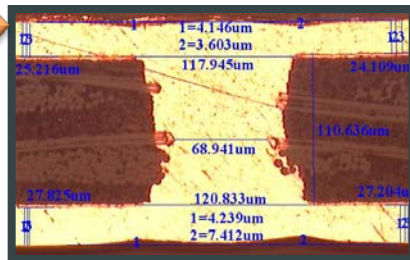


## DSLTH

100  $\mu$ m x 100 $\mu$ m

Electroless thickness:

0.2-0.5  $\mu$ m

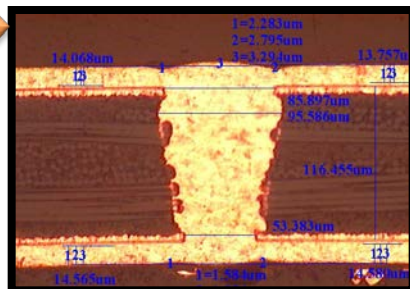


## OSLTH

100  $\mu$ m x 100 $\mu$ m

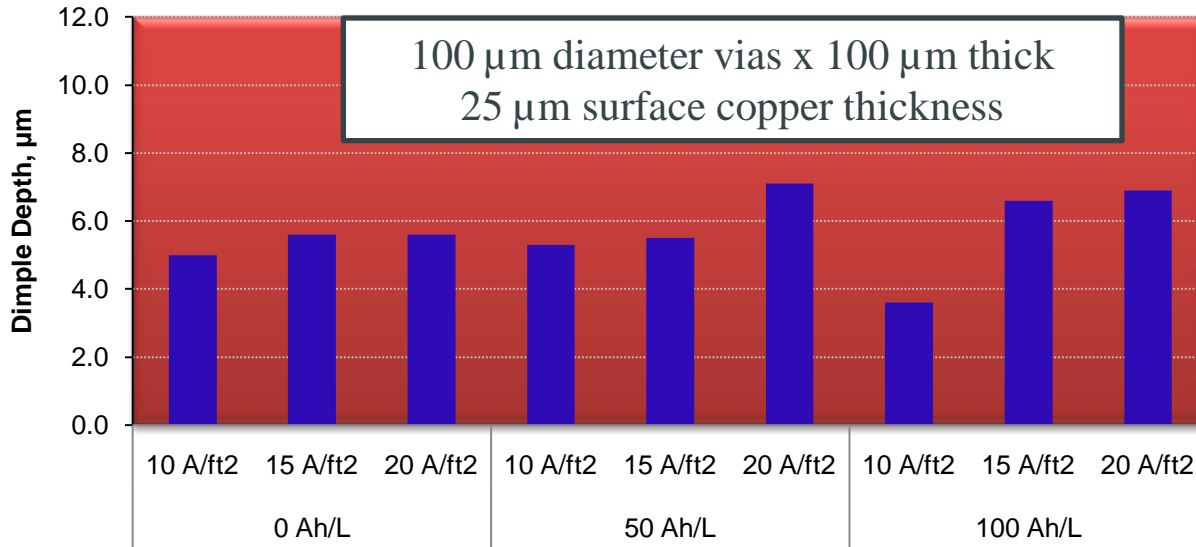
Flash copper thickness:

1.0-4.0  $\mu$ m



- THF performance is similar whether used with medium or low build electroless
- The quality and thickness of electroless copper affects THF performance
- THF performance decreases with decreasing electroless copper coverage
- The impact of poor coverage on THF performance is greater for low build electroless
- THF can be used also with electrolytic copper flashed substrates

# Fill Performance as a Function of Bath Age

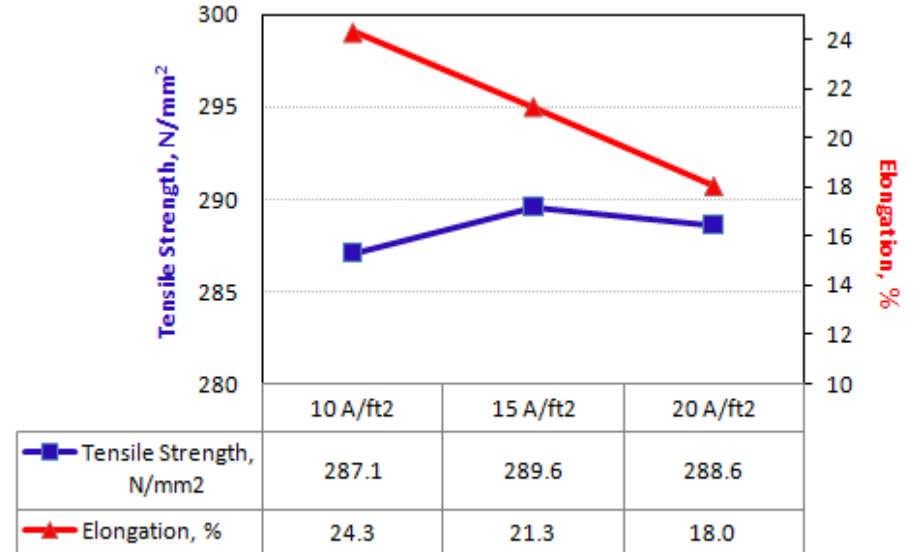
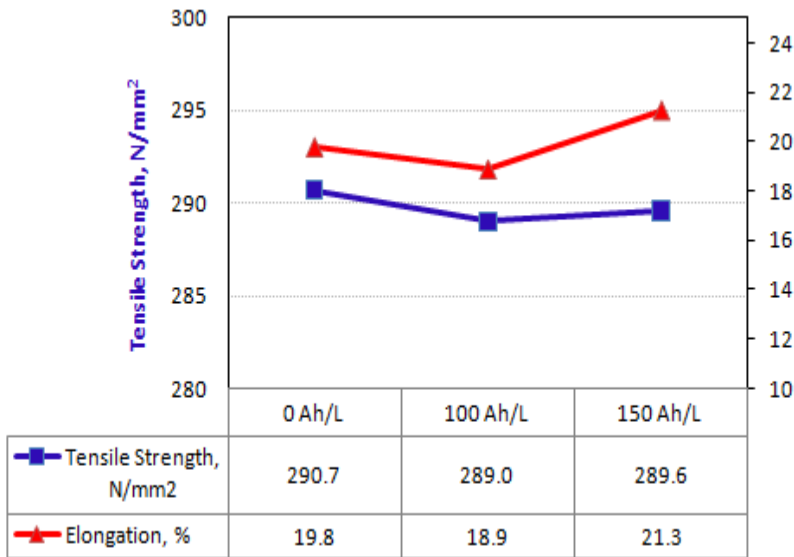


Consistent through hole fill performance with low dimple depth < 10 µm

Bath Age	10 A/ft <sup>2</sup>	15 A/ft <sup>2</sup>	20 A/ft <sup>2</sup>
0 Ah/L			
100 Ah/L			

Bath Age	100 µm dia x 100 µm thick	100 µm dia x 200 µm thick
0 Ah/L		
150 Ah/L		

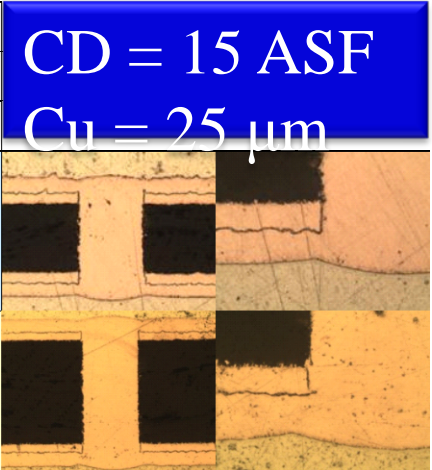
# Through Hole Fill Deposit Physical Properties





*Tensile Strength and Elongation measured per IPC-TM 650 2.4.18.1*

# Through Hole Fill Reliability

## Thermal Stress IPC-TM 650 2.6.8

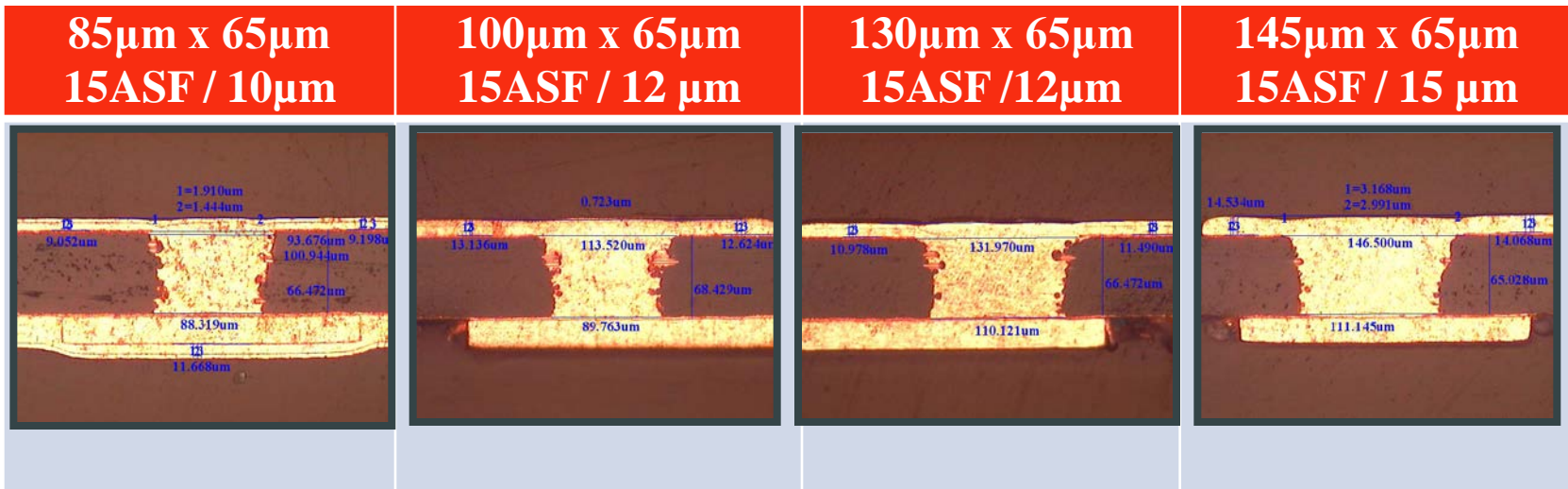
Hole Size	THF Bath Age				
	0 Ah/L	50 Ah/L	100 Ah/L	150 Ah/L	
	Number of cracks / number of holes				
100 μm dia x 100 μm thick	0/120	0/120	0/120	0/120	
100 μm dia x 200 μm thick	0/120	0/120	0/120	0/120	

CD (ASF) / Panel Thickness	Defects/ Total Holes Inspected	Cross Section
25 / 100 μm	0 / 220	
25 / 200 μm	0 / 220	

Excellent deposit performance throughout the range of bath age and current densities evaluated

# Blind Microvia Fill Performance

- MICROFILL™ THF bath can also be utilized for the metallization of Blind Micro Via (BMV) with surface copper thicknesses of less than 15  $\mu\text{m}$ . This system may be utilized for BMV plating for Every Layer Interconnect (ELIC) HDI and IC substrate applications.





## Conclusion

- Product is commercialized world wide. DC through hole fill process developed for HDI and IC package substrate.
- Consistent through hole fill performance with low dimple depth  $< 10 \mu\text{m}$
- Excellent fill performance, with mechanically drilled holes, and laser drilled holes
- High filling performance on substrates metallized with different thicknesses of electroless copper
- Excellent fill performance with dimple  $< 10 \mu\text{m}$  at range of CD up to 25 ASF
- Good deposit physical properties. Solder Float results showed no cracks.
- Depending on hole geometry, the MICROFILL™ THF Bath demonstrates superb filling performance with surface copper thickness between  $15\mu\text{m}$  and  $25\mu\text{m}$ .
- Highly leveled surface free of nodules and pits. All bath additive components can be monitored by CVS
- Excellent blind microvia fill performance.



**Thank  
You**

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